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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, SAI, SD, SPDIF-Rx, SPI, UART/USART, USB, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	50
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f446rct6tr

1 Introduction

This document provides the description of the STM32F446xC/E products.

The STM32F446xC/E document should be read in conjunction with the STM32F4xx reference manual.

For information on the Cortex®-M4 core, please refer to the Cortex®-M4 programming manual (PM0214), available from the *www.st.com*.

Figure 2. Compatible board for LQFP64 package

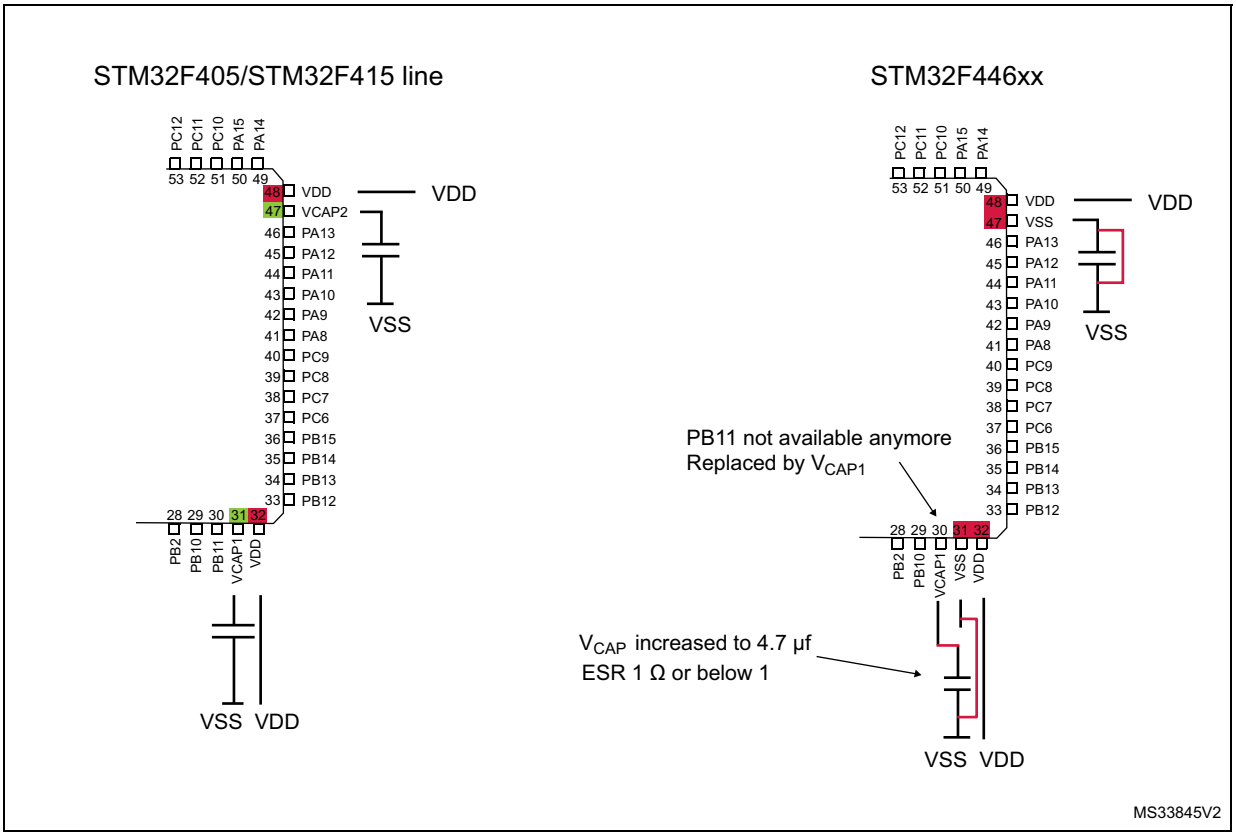


Figure 3 shows the STM32F446xx block diagram.

3 Functional overview

3.1 ARM® Cortex®-M4 with FPU and embedded Flash and SRAM

The ARM® Cortex®-M4 with FPU processor is the latest generation of ARM processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The ARM® Cortex®-M4 with FPU core is a 32-bit RISC processor that features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

The processor supports a set of DSP instructions which allow efficient signal processing and complex algorithm execution.

Its single precision FPU (floating point unit) speeds up software development by using metalanguage development tools, while avoiding saturation.

The STM32F446xC/E family is compatible with all ARM tools and software.

Figure 3 shows the general block diagram of the STM32F446xC/E family.

Note: Cortex-M4 with FPU core is binary compatible with the Cortex-M3 core.

3.2 Adaptive real-time memory accelerator (ART Accelerator™)

The ART Accelerator™ is a memory accelerator which is optimized for STM32 industry-standard ARM® Cortex®-M4 with FPU processors. It balances the inherent performance advantage of the ARM® Cortex®-M4 with FPU over Flash memory technologies, which normally requires the processor to wait for the Flash memory at higher frequencies.

To release the processor full 225 DMIPS performance at this frequency, the accelerator implements an instruction prefetch queue and branch cache, which increases program execution speed from the 128-bit Flash memory. Based on CoreMark benchmark, the performance achieved thanks to the ART Accelerator is equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 180 MHz.

3.3 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

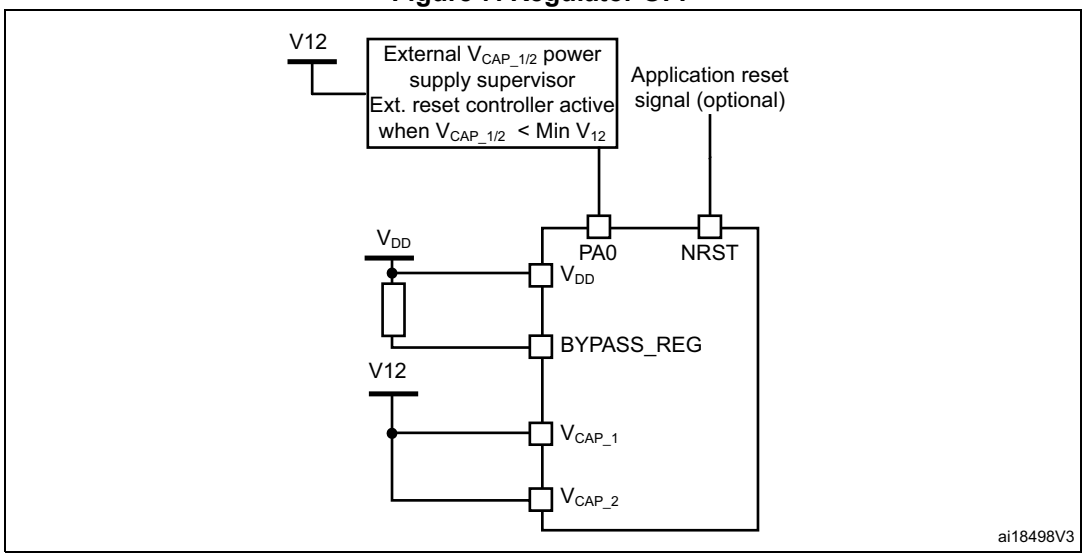
Since the internal voltage scaling is not managed internally, the external voltage value must be aligned with the targeted maximum frequency. The two 2.2 µF ceramic capacitors should be replaced by two 100 nF decoupling capacitors.

When the regulator is OFF, there is no more internal monitoring on V_{12}. An external power supply supervisor should be used to monitor the V_{12} of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V_{12} power domain.

In regulator OFF mode, the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the V_{12} logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.
- The over-drive and under-drive modes are not available.

Figure 7. Regulator OFF

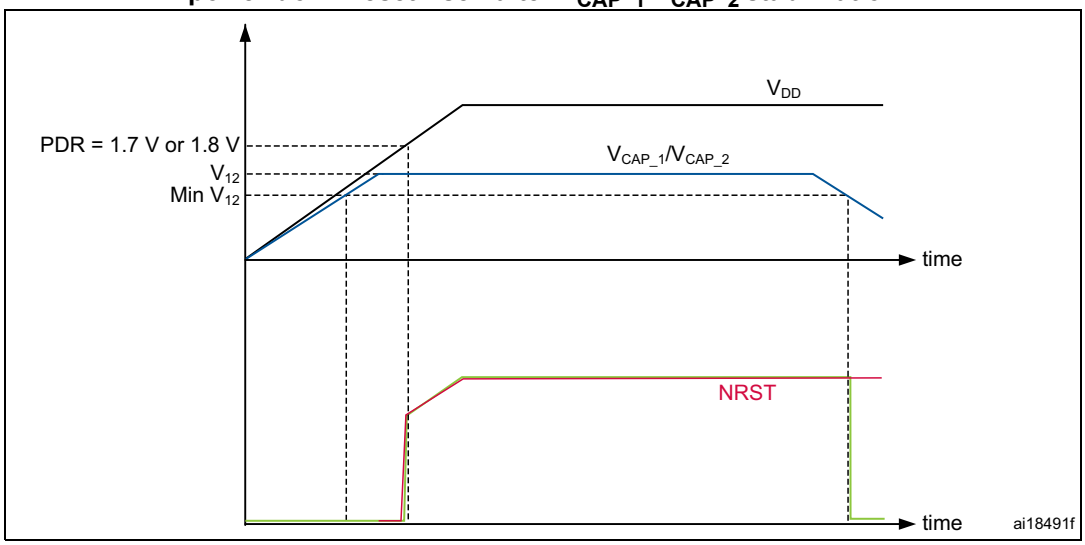


The following conditions must be respected:

- V_{DD} should always be higher than V_{CAP_1} and V_{CAP_2} to avoid current injection between power domains.
- If the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is faster than the time for V_{DD} to reach 1.7 V, then PA0 should be kept low to cover both conditions: until V_{CAP_1} and V_{CAP_2} reach V_{12} minimum value and until V_{DD} reaches 1.7 V (see *Figure 8*).
- Otherwise, if the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is slower than the time for V_{DD} to reach 1.7 V, then PA0 could be asserted low externally (see *Figure 9*).
- If V_{CAP_1} and V_{CAP_2} go below V_{12} minimum value and V_{DD} is higher than 1.7 V, then a reset must be asserted on PA0 pin.

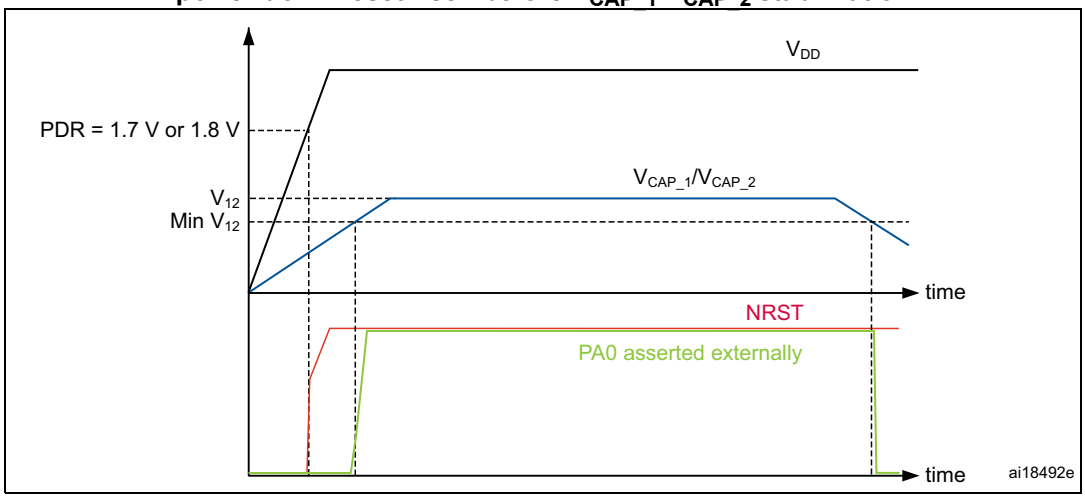
Note: The minimum value of V_{12} depends on the maximum frequency targeted in the application.

Figure 8. Startup in regulator OFF: slow V_{DD} slope power-down reset risen after V_{CAP_1}/V_{CAP_2} stabilization



1. This figure is valid whatever the internal reset mode (ON or OFF).

Figure 9. Startup in regulator OFF mode: fast V_{DD} slope power-down reset risen before V_{CAP_1}/V_{CAP_2} stabilization



1. This figure is valid whatever the internal reset mode (ON or OFF).

3.17.3 Regulator ON/OFF and internal reset ON/OFF availability

Table 4. Regulator ON/OFF and internal reset ON/OFF availability

Package	Regulator ON	Regulator OFF	Internal reset ON	Internal reset OFF
LQFP64 LQFP100	Yes	No	Yes	No

Table 10. STM32F446xx pin and ball descriptions (continued)

Pin Number					Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP64	LQFP100	WLCSP 81	UFBGA144	LQFP144						
63	99	B7	E6	-	VSS	S	-	-	-	-
-	-	B8	E5	143	PDR_ON	S	-	-	-	-
64	100	A8	F5	144	VDD	S	-	-	-	-

1. PA11, PA12, PB14 and PB15 I/Os are supplied by VDDUSB

Table 11. Alternate function (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11/CEC	I2C1/2/3/4/CEC	SPI1/2/3/4	SPI2/3/4/SAI1	SPI2/3/USART1/2/3/UART5/SPDIFRX	SAI/USART6/UART4/5/SPDIFRX	CAN1/2 TIM12/13/14/QUADSPI	SAI2/QUADSPI/OTG2_HS/OTG1_FS	OTG1_FS	FMC/SDIO/OTG2_FS	DCMI	-	SYS
Port H	PH0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PH1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT

1. The DCMI_VSYNC alternate function on PG9 is only available on silicon revision 3.

Table 12. STM32F446xC/E register boundary addresses(1)

Bus	Boundary address	Peripheral
-	0xE00F FFFF - 0xFFFF FFFF	Reserved
Cortex-M4	0xE000 0000 - 0xE00F FFFF	Cortex-M4 internal peripherals
AHB3	0xD000 0000 - 0xDFFF FFFF	FMC bank 6
	0xC000 0000 - 0xCFFF FFFF	FMC bank 5
	0xA000 2000 - 0x0xBFFF FFFF	Reserved
	0xA000 1000 - 0x0xA000 1FFF	QuadSPI control register
	0xA000 0000 - 0xA000 0FFF	FMC control register
	0x9000 0000 - 0x9FFF FFFF	QuadSPI
	0x8000 0000 - 0x8FFF FFFF	FMC bank 3
	0x7000 0000 - 0x0x7FFF FFFF	Reserved
	0x6000 0000 - 0x6FFF FFFF	FMC bank 1
-	0x5006 0C00- 0x5FFF FFFF	Reserved
AHB2	0x5006 0800- 0x500F 07FF	Reserved
	0x5005 0400 - 0x5006 07FF	Reserved
	0x5005 0000 - 0x5005 03FF	DCMI
	0x5004 0000- 0x5004 FFFF	Reserved
	0x5000 0000 - 0X5003 FFFF	USB OTG FS

Table 12. STM32F446xC/E register boundary addresses[1] (continued)

Bus	Boundary address	Peripheral
-	0x4008 0000- 0x4FFF FFFF	Reserved
AHB1	0x4004 0000 - 0x4007 FFFF	USB OTG HS
	0x4002 BC00- 0x4003 FFFF	Reserved
	0x4002 B000 - 0x4002 BBFF	
	0x4002 9400 - 0x4002 AFFF	
	0x4002 9000 - 0x4002 93FF	
	0x4002 8C00 - 0x4002 8FFF	
	0x4002 8800 - 0x4002 8BFF	
	0x4002 8400 - 0x4002 87FF	
	0x4002 8000 - 0x4002 83FF	
	0x4002 6800 - 0x4002 7FFF	
	0x4002 6400 - 0x4002 67FF	DMA2
	0x4002 6000 - 0x4002 63FF	DMA1
	0X4002 5000 - 0X4002 5FFF	Reserved
	0x4002 4000 - 0x4002 4FFF	BKPSRAM
	0x4002 3C00 - 0x4002 3FFF	Flash interface register
	0x4002 3800 - 0x4002 3BFF	RCC
	0X4002 3400 - 0X4002 37FF	Reserved
	0x4002 3000 - 0x4002 33FF	CRC
	0x4002 2C00 - 0x4002 2FFF	Reserved
	0x4002 2800 - 0x4002 2BFF	
	0x4002 2400 - 0x4002 27FF	
	0x4002 2000 - 0x4002 23FF	
	0x4002 1C00 - 0x4002 1FFF	GPIOH
	0x4002 1800 - 0x4002 1BFF	GPIOG
	0x4002 1400 - 0x4002 17FF	GPIOF
	0x4002 1000 - 0x4002 13FF	GPIOE
	0X4002 0C00 - 0x4002 0FFF	GPIOD
	0x4002 0800 - 0x4002 0BFF	GPIOC
	0x4002 0400 - 0x4002 07FF	GPIOB
	0x4002 0000 - 0x4002 03FF	GPIOA

Table 33. Typical current consumption in Sleep mode, regulator OFF(1)

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	VDD=3.3 V		VDD=1.7 V		Unit
				I_{DD12}	I_{DD}	I_{DD12}	I_{DD}	-
I_{DD12}/I_{DD}	Supply current in Sleep mode from V_{12} and V_{DD} supply	All Peripherals enabled	180	47.605	1.2	NA	NA	mA
			168	44.35	1.0	41.53	0.8	
			150	40.58	0.9	39.96	0.8	
			144	35.68	0.9	34.60	0.7	
			120	27.30	0.9	29.11	0.7	
			90	20.69	0.8	19.78	0.6	
			60	13.88	0.7	13.36	0.6	
			30	7.66	0.7	7.85	0.6	
			25	6.49	0.7	6.66	0.5	
		All Peripherals disabled	180	8.71	1.2	NA	NA	
			168	7.00	0.9	8.42	0.8	
			150	6.88	0.9	7.61	0.8	
			144	6.29	0.9	6.99	0.7	
			120	4.87	0.9	5.95	0.7	
			90	3.78	0.8	3.96	0.6	
			60	2.66	0.7	2.80	0.6	
			30	1.65	0.7	1.74	0.6	
			25	1.45	0.7	1.52	0.5	

1. When peripherals are enabled, the power consumption corresponding to the analog part of the peripherals (such as ADC, or DAC) is not included.

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 56: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Figure 23. High-speed external clock source AC timing diagram

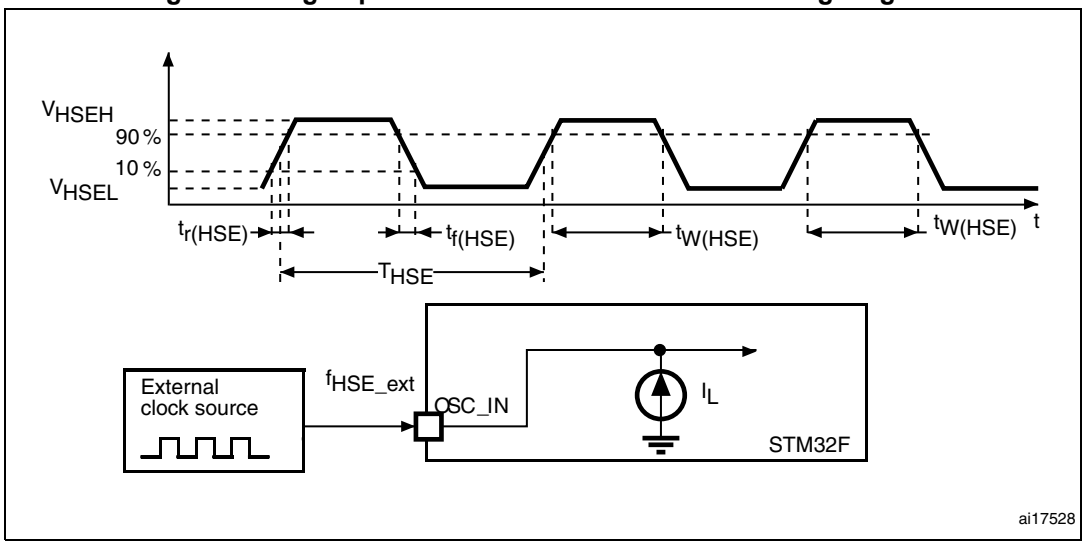
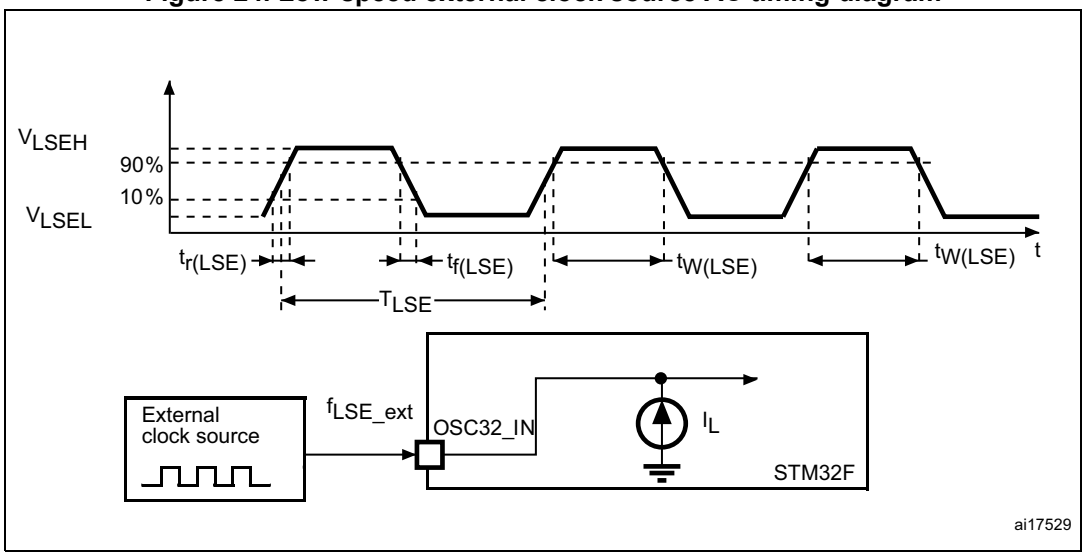


Figure 24. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 26 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 39*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

6.3.10 Internal clock source characteristics

The parameters given in *Table 41* and *Table 42* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 16*.

High-speed internal (HSI) RC oscillator

Table 41. HSI oscillator characteristics (1)

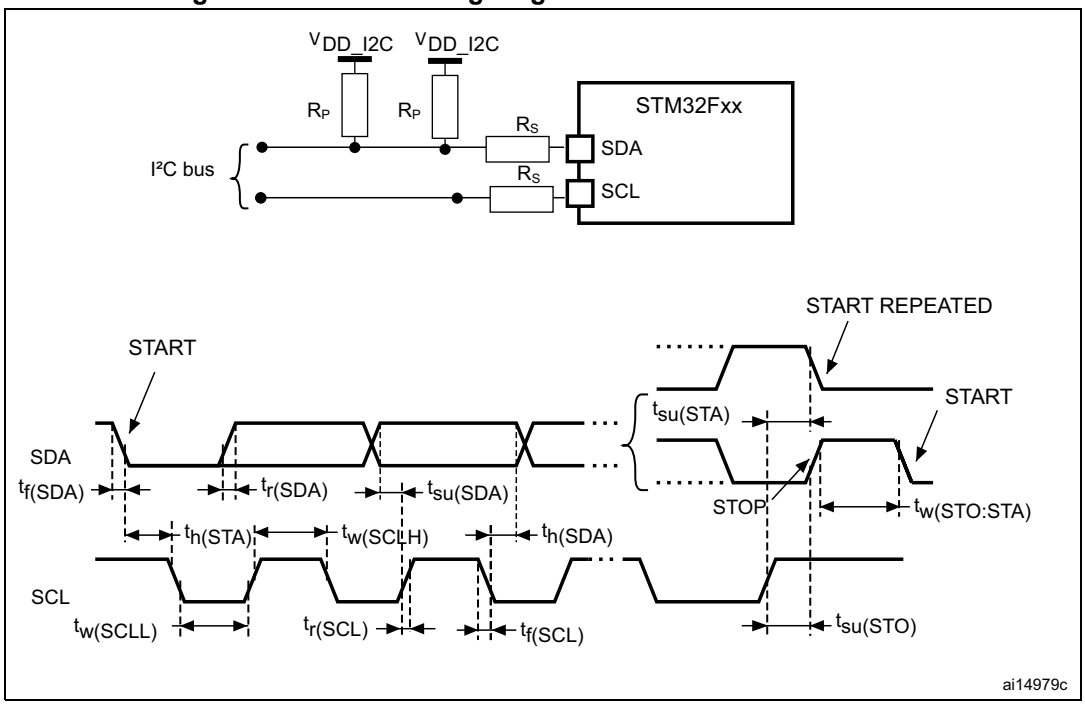
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	16	-	MHz
ACC_{HSI}	Accuracy of the HSI oscillator	User-trimmed with the RCC_CR register(2)	-	-	1	%
		T_A = - 40 to 105 °C(3)	- 8	-	4.5	%
		T_A = - 10 to 85 °C(3)	- 4	-	4	%
		T_A = 25 °C(4)	- 1	-	1	%
$t_{su(HSI)}$(2)	HSI oscillator startup time	-	-	2.2	4	µs
$I_{DD(HSI)}$(2)	HSI oscillator power consumption	-	-	60	80	µA

1. V_{DD} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design.
3. Guaranteed based on test during characterization.
4. Factory calibrated, parts not soldered.

Figure 27. $LACC_{HSI}$ versus temperature

1. Guaranteed based on test during characterization.

Figure 35. FMPI^{2}C timing diagram and measurement circuit



QSPI interface characteristics

Unless otherwise specified, the parameters given in *Table 64* for QSPI are derived from tests performed under the ambient temperature, f_{AHB} frequency and V_{DD} supply voltage conditions summarized in *Table 16*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C=20pF
- Measurement points are done at CMOS levels: 0.5VDD

Refer to *Section 6.3.17: I/O port characteristics* for more details on the input/output alternate function characteristics.

Table 64. QSPI dynamic characteristics in SDR Mode(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	QSPI clock frequency	Write mode 1.71 V≤V_{DD}≤3.6 V Cload = 15 pF	-	-	90	MHz
		Read mode 2.7V <VDD< 3.6V Cload = 15 pF	-	-	90	
		1.71 V≤V_{DD}≤3.6 V	-	-	48	
$t_{w(CKH)}$	QSPI clock high and low	-	($T_{(CK)}$ / 2) - 2	-	$T_{(CK)}$ / 2	ns
$t_{w(CKL)}$			$T_{(CK)}$ / 2	-	($T_{(CK)}$ / 2) +2	
$t_{s(IN)}$	Data input setup time	-	2	-	-	
$t_{h(IN)}$	Data input hold time	-	4.5	-	-	
$t_{v(OUT)}$	Data output valid time	-	-	1.5	3	
$t_{h(OUT)}$	Data output hold time	-	0	-	-	

1. Guaranteed based on test during characterization.

Table 65. QSPI dynamic characteristics in DDR Mode(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	QSPI clock frequency	Write mode 1.71 V≤V_{DD}≤3.6 V Cload = 15 pF	-	-	60	MHz
		Read mode 2.7V <VDD< 3.6V Cload = 15 pF	-	-	60	
		1.71 V≤V_{DD}≤3.6 V	-	-	48	

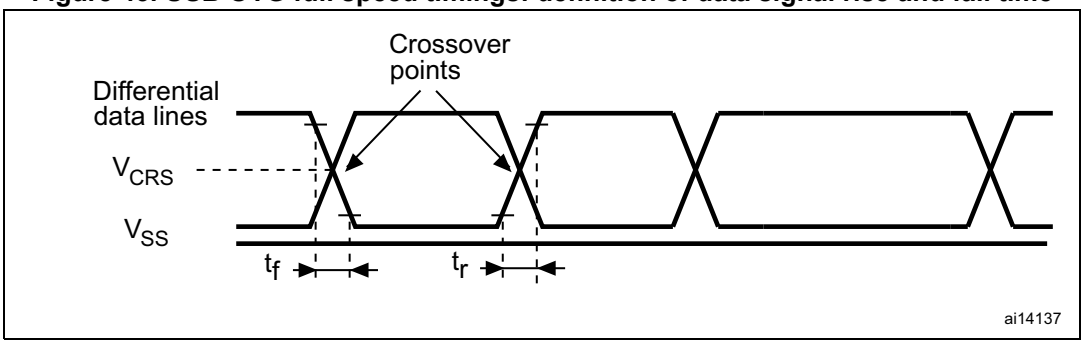
Table 69. USB OTG full speed DC electrical characteristics

Symbol		Parameter	Conditions	Min.(1)	Typ.	Max.(1)	Unit
Input levels	V_{DDUSB}	USB OTG full speed transceiver operating voltage	-	3.0(2)	-	3.6	V
	V_{DI}(3)	Differential input sensitivity	I(USB_FS_DP/DM, USB_HS_DP/DM)	0.2	-	-	V
	V_{CM}(3)	Differential common mode range	Includes V_{DI} range	0.8	-	2.5	
	V_{SE}(3)	Single ended receiver threshold	-	1.3	-	2.0	
Output levels	V_{OL}	Static output level low	R_L of 1.5 kΩ to 3.6 V(4)	-	-	0.3	V
	V_{OH}	Static output level high	R_L of 15 kΩ to V_{SS}(4)	2.8	-	3.6	
R_{PD}		PA11, PA12, PB14, PB15 (USB_FS_DP/DM, USB_HS_DP/DM)	V_{IN} = V_{DDUSB}	17	21	24	kΩ
		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)		0.65	1.1	2.0	
R_{PU}		PA12, PB15 (USB_FS_DP, USB_HS_DP)	V_{IN} = V_{SS}	1.5	1.8	2.1	
		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	V_{IN} = V_{SS}	0.25	0.37	0.55	

1. All the voltages are measured from the local ground potential.
2. The USB OTG full speed transceiver functionality is ensured down to 2.7 V but not the full USB full speed electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
3. Guaranteed by design.
4. R_L is the load connected on the USB OTG full speed drivers.

Note: When VBUS sensing feature is enabled, PA9 and PB13 should be left at their default state (floating input), not as alternate function. A typical 200 µA current consumption of the sensing block (current to voltage conversion to determine the different sessions) can be observed on PA9 and PB13 when the feature is enabled.

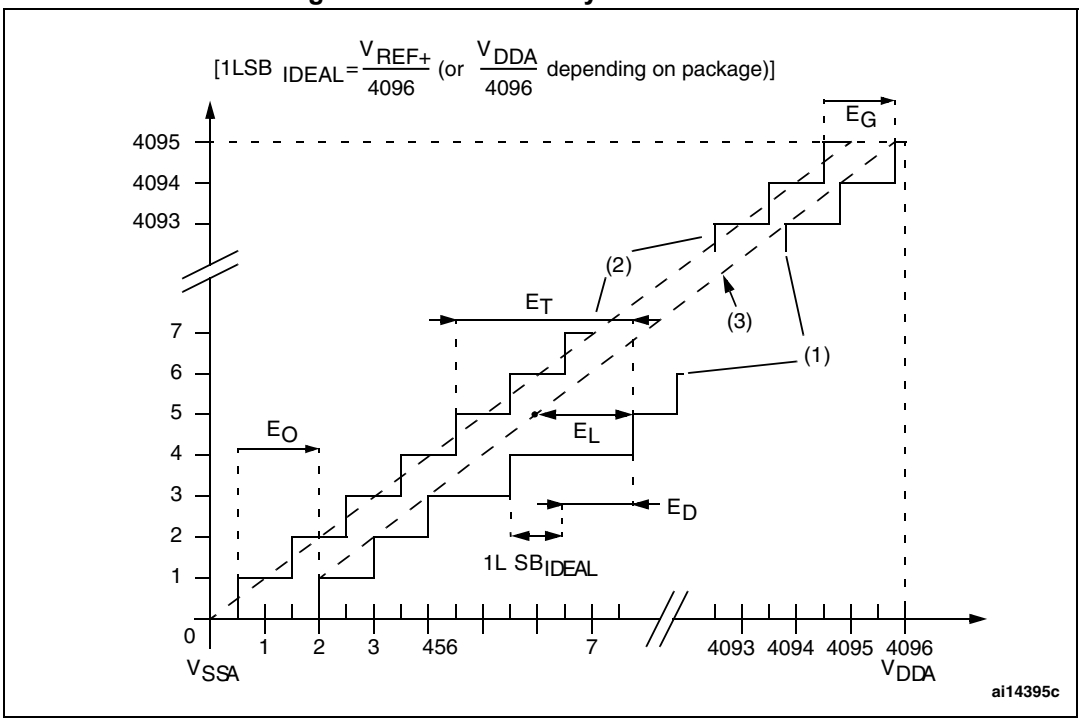
Figure 43. USB OTG full speed timings: definition of data signal rise and fall time



being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.17* does not affect the ADC accuracy.

Figure 45. ADC accuracy characteristics



1. See also *Table 76*.
2. Example of an actual transfer curve.
3. Ideal transfer curve.
4. End point correlation line.
5. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
   EO = Offset Error: deviation between the first actual transition and the first ideal one.
   EG = Gain Error: deviation between the last ideal transition and the last actual one.
   ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
   EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Table 85. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	Comments
INL(4)	Integral non linearity (difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	-	±1	LSB	Given for the DAC in 10-bit configuration.
		-	-	-	±4	LSB	Given for the DAC in 12-bit configuration.
Offset(4)	Offset error (difference between measured value at Code (0x800) and the ideal value = $V_{REF+}/2$)	-	-	-	±10	mV	Given for the DAC in 12-bit configuration
		-	-	-	±3	LSB	Given for the DAC in 10-bit at V_{REF+} = 3.6 V
		-	-	-	±12	LSB	Given for the DAC in 12-bit at V_{REF+} = 3.6 V
Gain error(4)	Gain error	-	-	-	±0.5	%	Given for the DAC in 12-bit configuration
$t_{SETTLING}$(4)	Total Harmonic Distortion Buffer ON	-	-	3	6	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
THD(4)	-	-	-	-	-	dB	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
Update rate(2)	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	-	1	MS/s	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
t_{WAKEUP}(4)	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	-	6.5	10	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ input code between lowest and highest possible ones.
PSRR+ (2)	Power supply rejection ratio (to V_{DDA}) (static DC measurement)	-	-	- 67	- 40	dB	No R_{LOAD}, C_{LOAD} = 50 pF

1. V_{DDA} minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to *Section 3.16.2: Internal reset OFF*).
2. Guaranteed by design.
3. The quiescent mode corresponds to a state where the DAC maintains a stable output level to ensure that no dynamic consumption occurs.
4. Guaranteed based on test during characterization.

Table 86. Asynchronous non-multiplexed SRAM/PSRAM/NOR - read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$2T_{HCLK} – 2$	$2\ T_{HCLK} + 0.5$	ns
$t_{v(NOE\_NE)}$	FMC_NEx low to FMC_NOE low	0	1	
$t_{w(NOE)}$	FMC_NOE low time	$2T_{HCLK} - 1$	$2T_{HCLK} + 0.5$	
$t_{h(NE\_NOE)}$	FMC_NOE high to FMC_NE high hold time	0	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0.5	
$t_{h(A\_NOE)}$	Address hold time after FMC_NOE high	0	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	2	
$t_{h(BL\_NOE)}$	FMC_BL hold time after FMC_NOE high	0	-	
$t_{su(Data\_NE)}$	Data to FMC_NEx high setup time	$T_{HCLK} - 2$	-	
$t_{su(Data\_NOE)}$	Data to FMC_NOEx high setup time	$T_{HCLK} - 2$	-	
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	-	0	
$t_{w(NADV)}$	FMC_NADV low time	-	$T_{HCLK} +1$	

1. C_L = 30 pF.
2. Guaranteed based on test during characterization.

Table 87. Asynchronous non-multiplexed SRAM/PSRAM/NOR read - NWAIT timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$7T_{HCLK} + 1$	$7T_{HCLK}$	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK} – 1$	$5T_{HCLK} + 1$	
$t_{w(NWAIT)}$	FMC_NWAIT low time	$T_{HCLK} – 0.5$	-	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK}+ 1.5$	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK} + 1$	-	

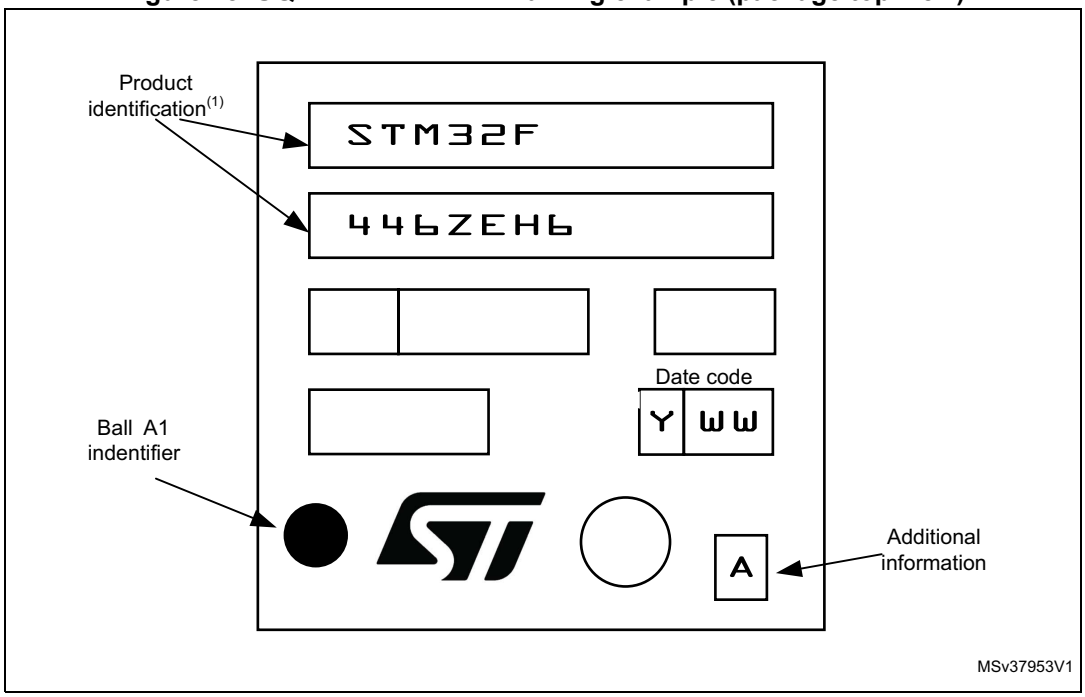
1. C_L = 30 pF.
2. Guaranteed based on test during characterization.

Device marking for UFBGA144 7 x 7 mm package

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 78. UQFP144 7 x 7 mm marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.